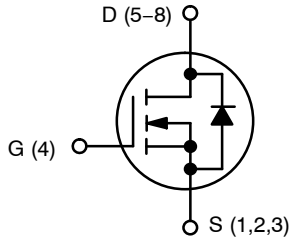
MOSFET - Power, Single N-Channel, DUAL COOL®, DFN8 5x6

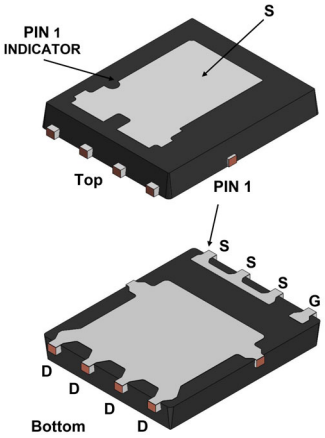
80 V, 1.4 mΩ, 270 A

NTMFSCH1D4N08X

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
80 V	1.4 mΩ @ 10 V	270 A



N−CHANNEL MOSFET



DFN8 5x6
CASE 506FF

Features

- Advanced Dual-Side Cool Package with Enhanced Heat−Dissipation Molding Compound
- Low Q_{RR}, Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_g to Minimize Gate Driving Losses
- MSL1 Robust Packaging Design
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Supply Unit (PSU)
- DC/DC Intermediated Bus Converter
- Motor Drives
- Synchronous Rectifier
- ORing

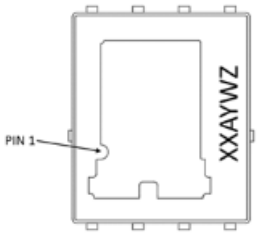
MAXIMUM RATINGS (T_J = 25 °C, Unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	80	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Notes 1, 2)	T_C = 25 °C	I_D	270	A
	T_C = 100 °C		191	
Power Dissipation (Notes 1, 2)	T_C = 25 °C	P_D	208	W
Pulsed Drain Current	T_C = 25 °C, t_p = 100 μs	I_{DM}	1110	A
Pulsed Source Current (Body Diode)		I_{SM}	1110	A
Operating Junction and Storage Temperature		T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)	T_C = 25 °C	I_S	231	A
Single Pulse Avalanche Energy (I_{pk} = 81 A) (Note 3)		E_{AS}	328	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8″ from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown. They are not constants and are only valid for the particular conditions noted.
2. Actual continuous current will be limited by thermal & electromechanical application board design.
3. EAS of 328 mJ is based on started T_J = 25 °C, I_{AS} = 81 A, V_{DD} = 64 V, V_{GS} = 10 V, 100% avalanche tested.

MARKING DIAGRAM



3V = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
Z = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case (Bottom)	$R_{\theta JCB}$	0.72	°C/W
Thermal Resistance, Junction-to-Case (Top)	$R_{\theta JCT}$	0.78	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	39	

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA, T_J = 25 °C	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 1 mA. Referenced to 25 °C		32		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, T_J = 25 °C			10	μA
		V_{DS} = 80 V, T_J = 125 °C			250	
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
ON CHARACTERISTICS						
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A, T_J = 25 °C		1.1	1.4	mΩ
		V_{GS} = 6 V, I_D = 30 A, T_J = 25 °C		1.7	2.4	
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 348 μA, T_J = 25 °C	2.4		3.6	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)}/\Delta T_J$	V_{GS} = V_{DS}, I_D = 348 μA		−7		mV/°C
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = 30 A		133		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, V_{DS} = 40 V, f = 1 MHz		6140		pF
Output Capacitance	C_{OSS}			1780		
Reverse Transfer Capacitance	C_{RSS}			27		
Output Charge	Q_{OSS}			130		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 6 V, V_{DD} = 40 V; I_D = 30 A		54		
		V_{GS} = 10 V, V_{DD} = 40 V; I_D = 30 A		86		
Threshold Gate Charge	$Q_{G(TH)}$			19		
Gate-to-Source Charge	Q_{GS}			28		
Gate-to-Drain Charge	Q_{GD}			13		
Gate Plateau Voltage	V_{GP}			4.6		V
Gate Resistance	R_G	f = 1 MHz		0.4		Ω
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, V_{GS} = 0/10 V, V_{DD} = 40 V, I_D = 30 A, R_G = 2.5 Ω		33		ns
Rise Time	t_r			9		
Turn-Off Delay Time	$t_{d(OFF)}$			50		
Fall Time	t_f			8		
SOURCE-TO-DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 30 A, T_J = 25 °C		0.8	1.2	V
		V_{GS} = 0 V, I_S = 30 A, T_J = 125 °C		0.6		

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SOURCE-TO-DRAIN DIODE CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI/dt = 1000 A/μs, I_S = 30 A, V_{DD} = 40 V, T_J = 25 °C		28		ns
Charge Time	t_a			16		
Discharge Time	t_b			12		
Reverse Recovery Charge	Q_{RR}			231		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

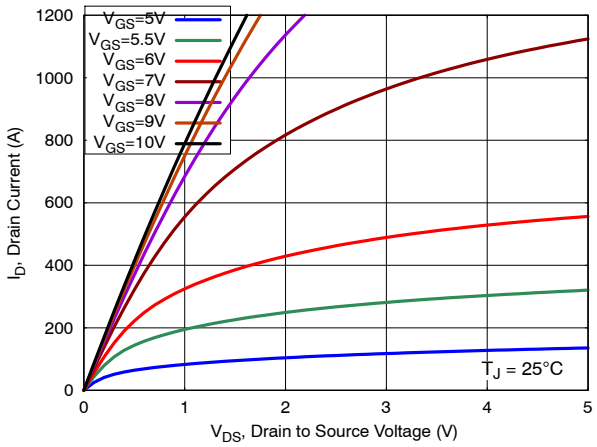


Figure 1. On-Region Characteristics

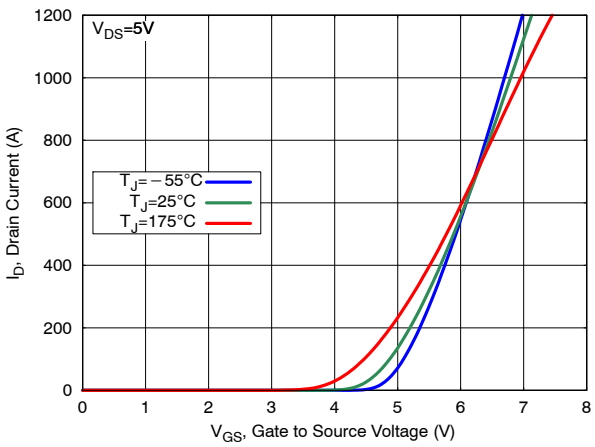


Figure 2. Transfer Characteristics

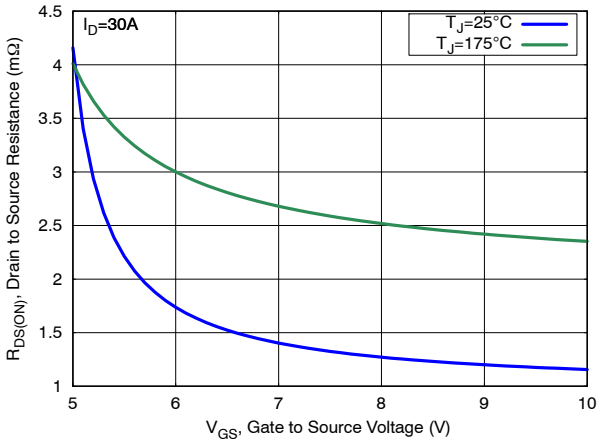


Figure 3. On-Resistance vs. Gate Voltage

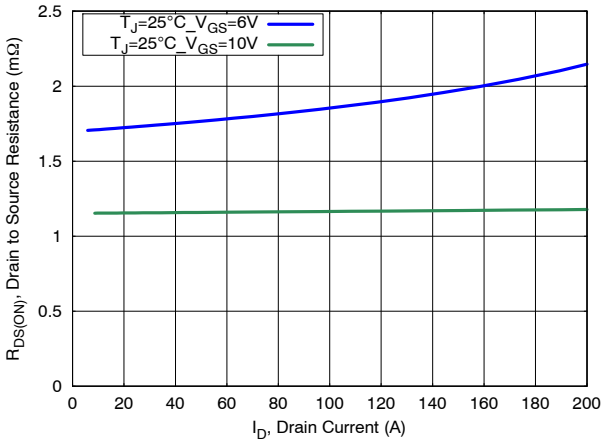


Figure 4. On-Resistance vs. Drain Current

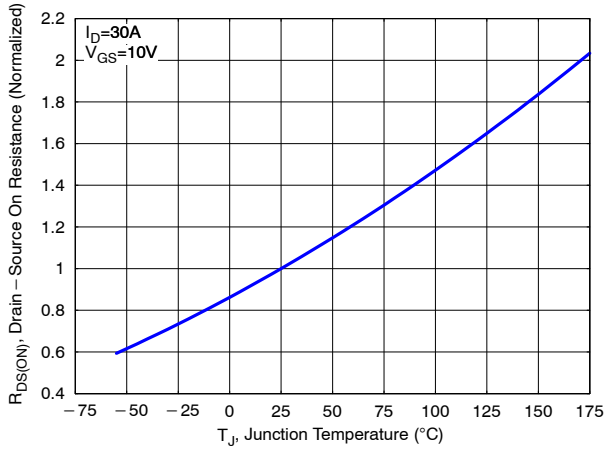


Figure 5. Normalized ON Resistance vs. Junction Temperature

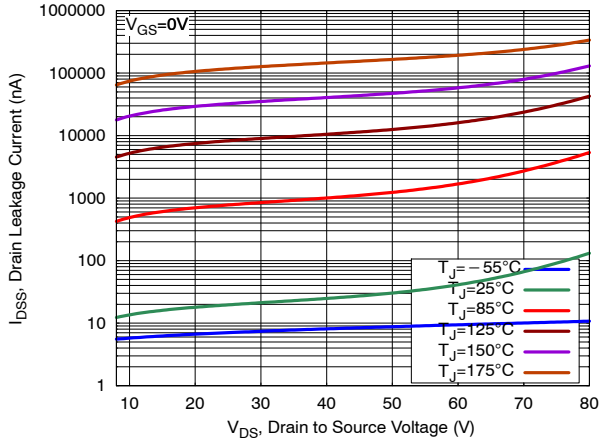


Figure 6. Drain Leakage Current vs Drain Voltage

TYPICAL CHARACTERISTICS

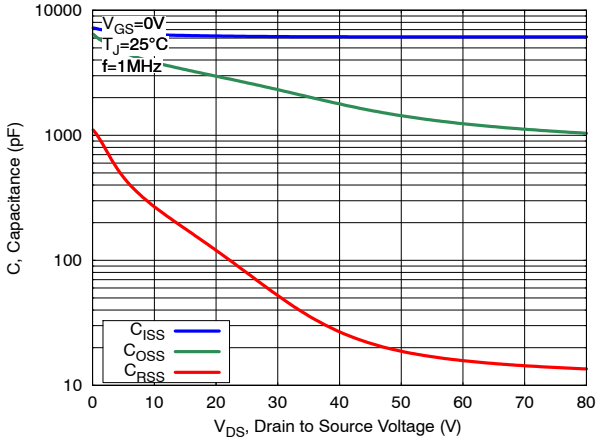


Figure 7. Capacitance Characteristics

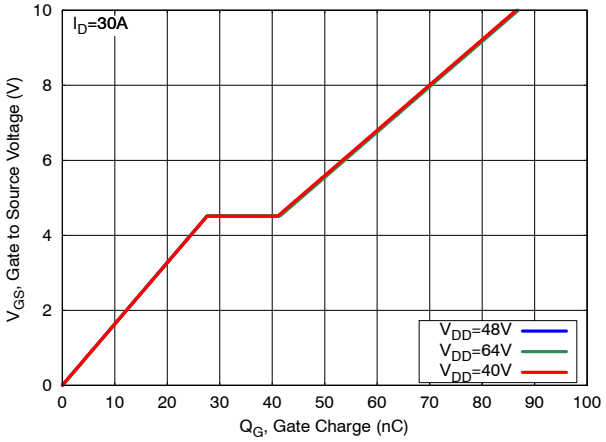


Figure 8. Gate Charge Characteristics

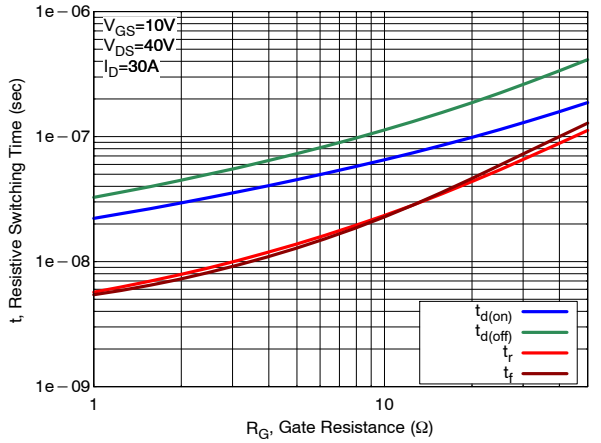


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

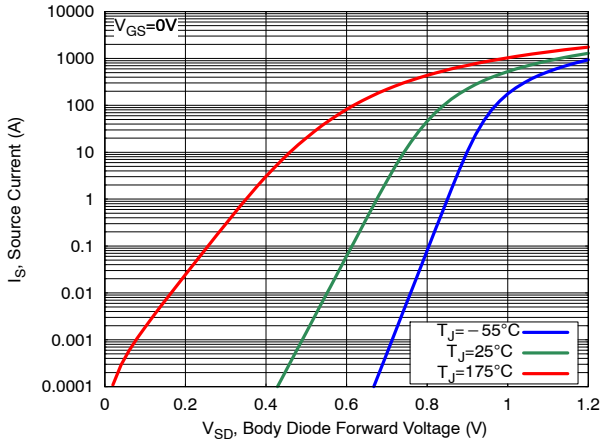


Figure 10. Diode Forward Characteristics

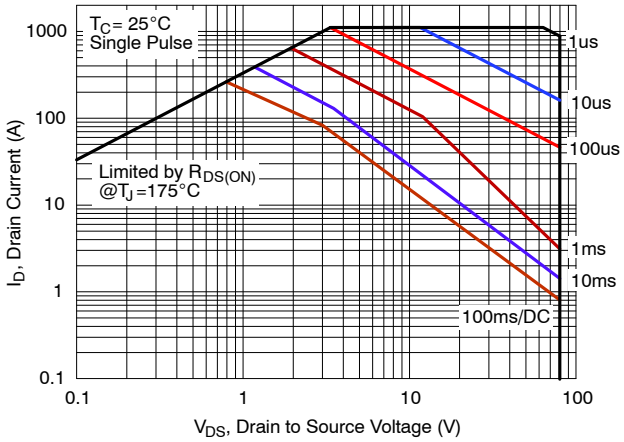


Figure 11. Safe Operating Area (SOA)

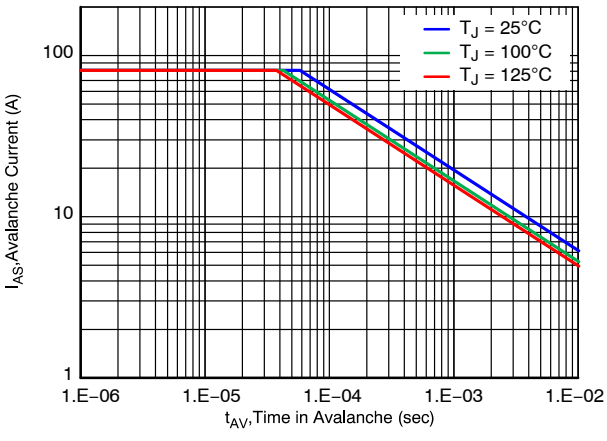


Figure 12. Avalanche Current vs Pulse Time (UIS)

TYPICAL CHARACTERISTICS

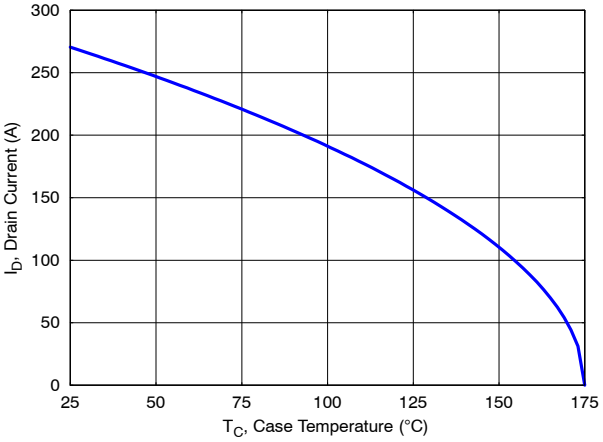


Figure 13. Maximum Current vs. Case Temperature

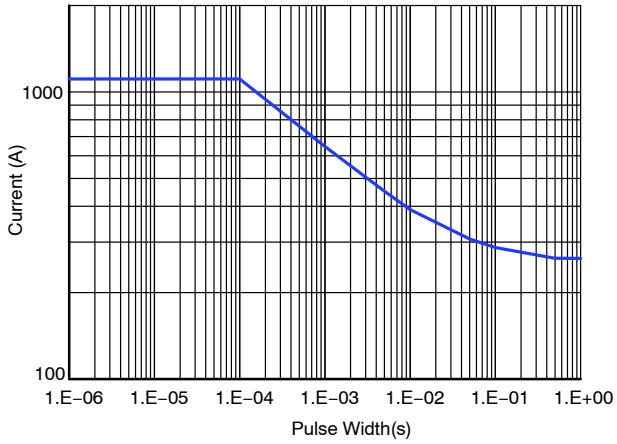


Figure 14. IDM vs. Pulse Width

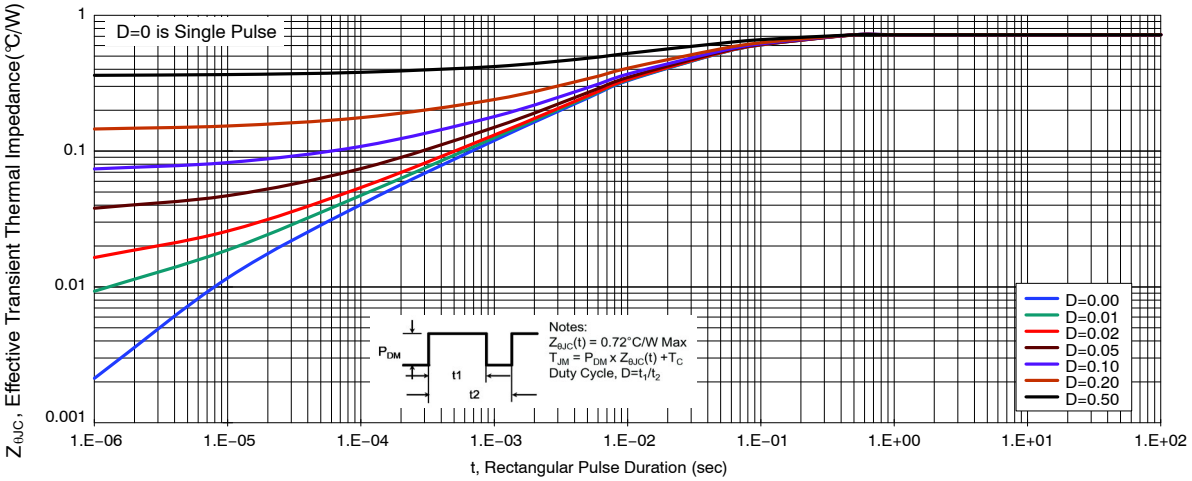


Figure 15. Transient Thermal Response

ORDERING INFORMATION

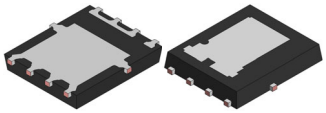
Device	Device Marking	Package	Shipping†
NTMFSCH1D4N08XTWG	3V	DFN8 5.1x6.15 (Pb-Free/Halogen Free)	3000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

REVISION HISTORY

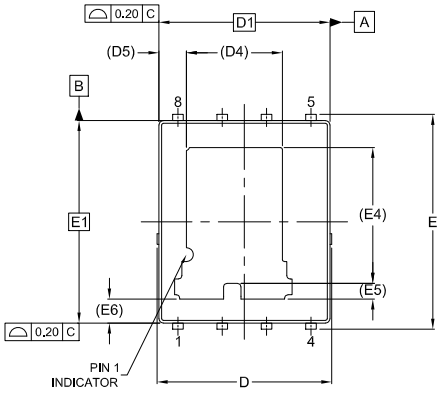
Revision	Description of Changes	Date
2	Final version release.	07/29/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

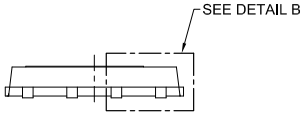


DFN8 4.90x5.80x0.90, 1.27P
CASE 506FF
ISSUE D

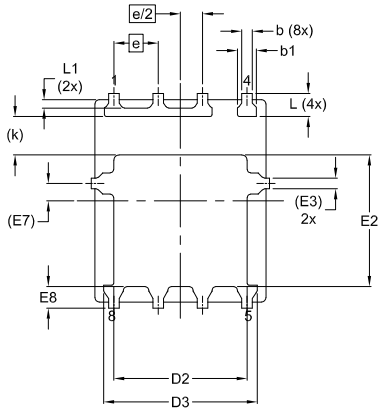
DATE 21 MAR 2025



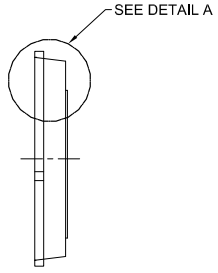
TOP VIEW



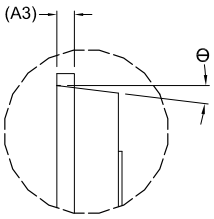
FRONT VIEW



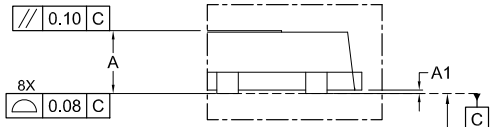
BOTTOM VIEW



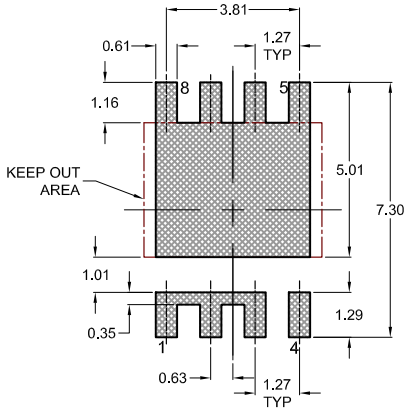
SIDE VIEW



DETAIL A
SCALE: 2:1



DETAIL B
SCALE: 2:1



LAND PATTERN
RECOMMENDATION

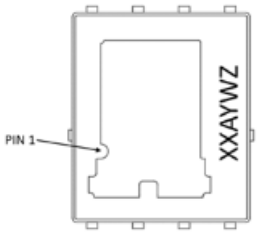
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.85	0.90	0.95
A1	-	-	0.05
A3		0.25 REF	
b	0.21	0.31	0.41
b1	0.44	0.54	0.64
D	4.90	5.00	5.10
D1		4.90 BSC	
D2	3.72	3.82	3.92
D3	4.30	4.40	4.50
D4		2.75 REF	
D5		0.79 REF	
E	6.05	6.15	6.25
E1		5.80 BSC	
E2	3.67	3.77	3.87
E3		0.30 REF	
E4		3.89 REF	
E5		0.45 REF	
E6		0.69 REF	
E7		0.50 REF	
E8	0.52	0.62	0.72
e		1.27 BSC	
e/2		0.635BSC	
k		1.10 REF	
L	0.56	0.66	0.76
L1	0.15	0.25	0.35
Θ	0°	---	7°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
Z = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON54466H	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	DFN8 4.90x5.80x0.90, 1.27P	PAGE 1 OF 1

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales